

# PMBTA42

# 300 V, 100 mA NPN high-voltage transistor Rev. 05 — 12 December 2008

Product data sheet

#### 1. **Product profile**

### 1.1 General description

NPN high-voltage transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

PNP complement: PMBTA92.

#### 1.2 Features

■ High voltage (max. 300 V)

### 1.3 Applications

Telephony and professional communication equipment

#### 1.4 Quick reference data

Quick reference data Table 1.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	300	V
I <sub>C</sub>	collector current		-	-	100	mA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 10 V				
		I <sub>C</sub> = 1 mA	25	-	-	
		I <sub>C</sub> = 10 mA	40	-	-	
		$I_C = 30 \text{ mA}$	40	-	-	

#### **Pinning information** 2.

Table 2. **Pinning** 

Pin	Description	Simplified outline	Graphic symbol
1	base	_	
2	emitter	3	3
3	collector	1 2	1 —
			sym021



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### 3. Ordering information

Table 3. Ordering information

Type number[1]	Package				
	Name	Description	Version		
PMBTA42	-	plastic surface-mounted package; 3 leads	SOT23		
PMBTA42/DG	_				

<sup>[1] /</sup>DG: halogen-free

### 4. Marking

Table 4. Marking codes

Type number[1]	Marking code <sup>[2]</sup>
PMBTA42	*1D
PMBTA42/DG	*BV

<sup>[1] /</sup>DG: halogen-free

## 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter	-	300	V
$V_{CEO}$	collector-emitter voltage	open base	-	300	V
$V_{EBO}$	emitter-base voltage	open collector	-	6	V
I <sub>C</sub>	collector current		-	100	mA
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	200	mA
I <sub>BM</sub>	peak base current	single pulse; $t_p \le 1 \text{ ms}$	-	100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	<u>[1]</u> -	250	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
$T_{\text{stg}}$	storage temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

<sup>[2] \* = -:</sup> made in Hong Kong

<sup>\* =</sup> p: made in Hong Kong

<sup>\* =</sup> t: made in Malaysia

<sup>\* =</sup> W: made in China

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### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	500	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

### 7. Characteristics

Table 7. Characteristics

 $T_{amb} = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$I_{CBO}$	collector-base cut-off current	$V_{CB} = 200 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 6 \text{ V}; I_C = 0 \text{ A}$	-	-	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 10 V				
		$I_C = 1 \text{ mA}$	25	-	-	
		$I_C = 10 \text{ mA}$	40	-	-	
		$I_C = 30 \text{ mA}$	40	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 20 \text{ mA}; I_B = 2 \text{ mA}$	-	-	500	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C = 20 \text{ mA}; I_B = 2 \text{ mA}$	-	-	900	mV
C <sub>re</sub>	feedback capacitance	$V_{CB} = 20 \text{ V}; I_C = I_c = 0 \text{ A};$ f = 1 MHz	-	-	3	pF
f <sub>T</sub>	transition frequency	$V_{CE} = 20 \text{ V}; I_{C} = 10 \text{ mA};$ f = 100 MHz	50	-	-	MHz

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### 8. Package outline

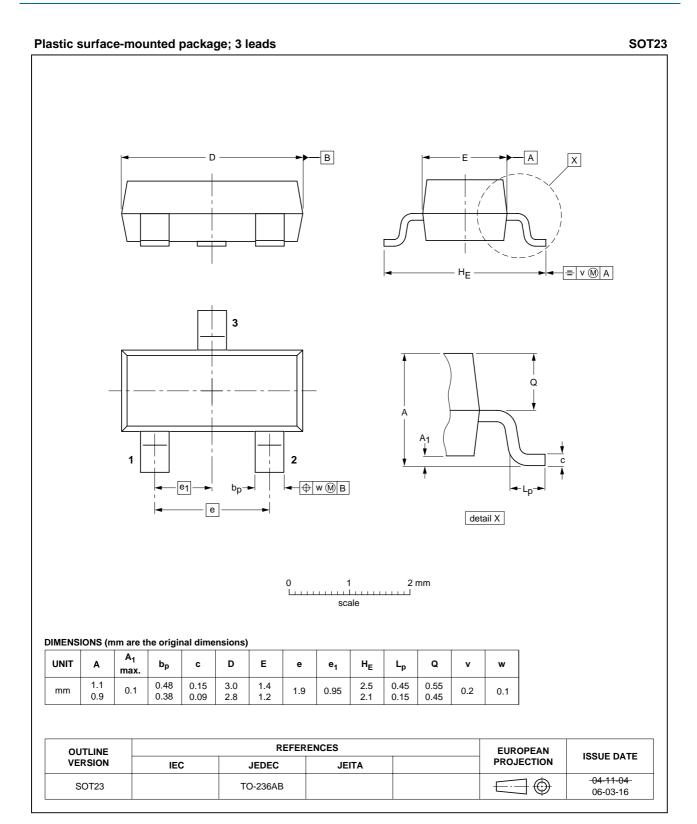


Fig 1. Package outline SOT23 (TO-236AB)

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### 9. Packing information

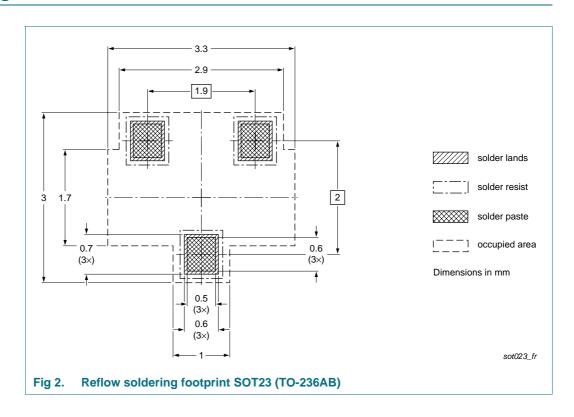
Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity	
			3000	10000
PMBTA42	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235
PMBTA42/DG				

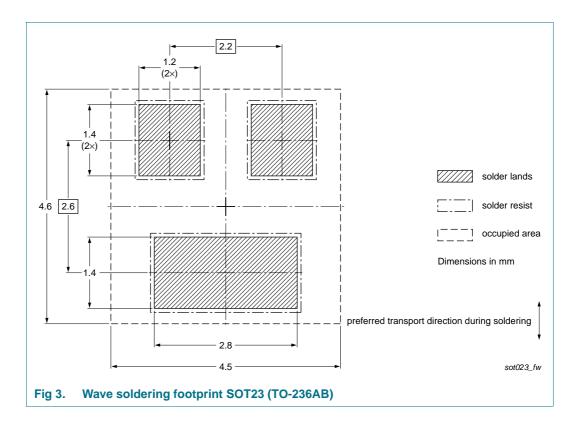
<sup>[1]</sup> For further information and the availability of packing methods, see Section 13.

### 10. Soldering



<sup>[2] /</sup>DG: halogen-free

### 300 V, 100 mA NPN high-voltage transistor



### 300 V, 100 mA NPN high-voltage transistor

### 11. Revision history

### Table 9. Revision history

	•					
Document ID	Release date	Data sheet status	Change notice	Supersedes		
PMBTA42_5	20081212	Product data sheet	-	PMBTA42_4		
Modifications:		of this data sheet has been of NXP Semiconductors.	redesigned to comply v	vith the new identity		
	<ul> <li>Legal texts have been adapted to the new company name where appropriate.</li> </ul>					
	<ul> <li>Type numb</li> </ul>	er PMBTA42/DG added				
	• Table 4 "Ma	arking codes": enhanced				
	• Section 12	"Legal information": update	d			
PMBTA42_4	20040122	Product specification	-	PMBTA42_3		
PMBTA42_3	19990422	Product specification	-	PMBTA42_43_CNV_2		

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### 12. Legal information

#### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
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